

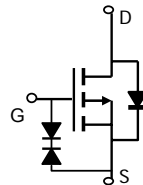
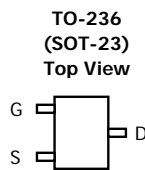
**AO3423**
**P-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO3423 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AO3423 is Pb-free (meets ROHS & Sony 259 specifications). AO3423L is a Green Product ordering option. AO3423 and AO3423L are electrically identical.*

**Features**

$V_{DS}$  (V) = -20V  
 $I_D$  = -2 A ( $V_{GS}$  = -10V)  
 $R_{DS(ON)}$  < 92m $\Omega$  ( $V_{GS}$  = -10V)  
 $R_{DS(ON)}$  < 118m $\Omega$  ( $V_{GS}$  = -4.5V)  
 $R_{DS(ON)}$  < 166m $\Omega$  ( $V_{GS}$  = -2.5V)  
 ESD Rating: 2000V HBM


**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}^F$	-2
		$T_A=70^\circ\text{C}^F$	-2
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-8	A
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	1.4
		$T_A=70^\circ\text{C}$	0.9
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	65	90	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	85	125
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	43	60	$^\circ\text{C/W}$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-20			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-0.5 -2.5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 10\text{V}$ $V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$			$\pm 1$ $\pm 10$	$\mu\text{A}$ $\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.7	-0.9	-1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$	-8			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-2\text{A}$ $T_J=125^\circ\text{C}$ $V_{GS}=-4.5\text{V}, I_D=-2\text{A}$ $V_{GS}=-2.5\text{V}, I_D=-1\text{A}$		76 90 94 128	92 108 118 166	$\text{m}\Omega$ $\text{m}\Omega$ $\text{m}\Omega$ $\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-2\text{A}$		6.8		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$	-1	-0.78		V
$I_S$	Maximum Body-Diode Continuous Current				-1.8	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$		512	620	pF
$C_{oss}$	Output Capacitance			77		pF
$C_{rss}$	Reverse Transfer Capacitance			62		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		9.2	13	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, I_D=-2\text{A}$		5.5	6.6	nC
$Q_{gs}$	Gate Source Charge			0.8		nC
$Q_{gd}$	Gate Drain Charge			1.9		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-10\text{V}, R_L=5\Omega,$ $R_{GEN}=3\Omega$		5		ns
$t_r$	Turn-On Rise Time			6.7		ns
$t_{D(off)}$	Turn-Off Delay Time			28		ns
$t_f$	Turn-Off Fall Time			13.5		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-2\text{A}, di/dt=100\text{A}/\mu\text{s}$		9.8	12	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-2\text{A}, di/dt=100\text{A}/\mu\text{s}$		2.7		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using  $80\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

F: The maximum current rating is limited by bond-wires.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

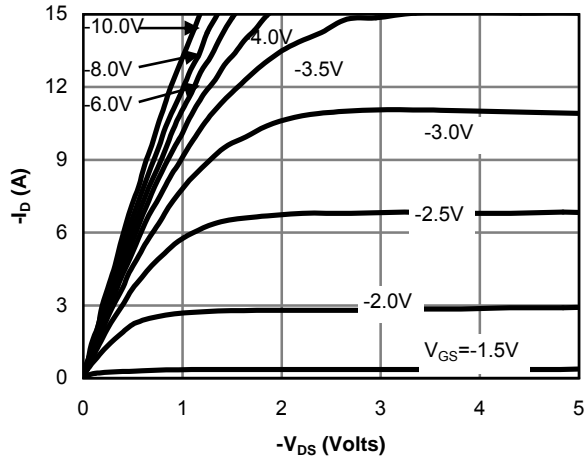


Fig 1: On-Region Characteristics

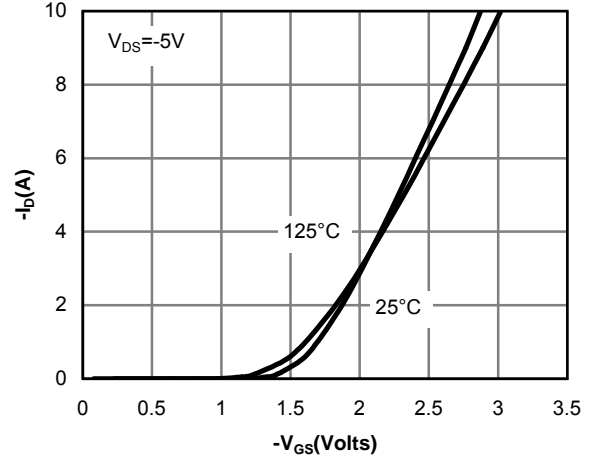


Figure 2: Transfer Characteristics

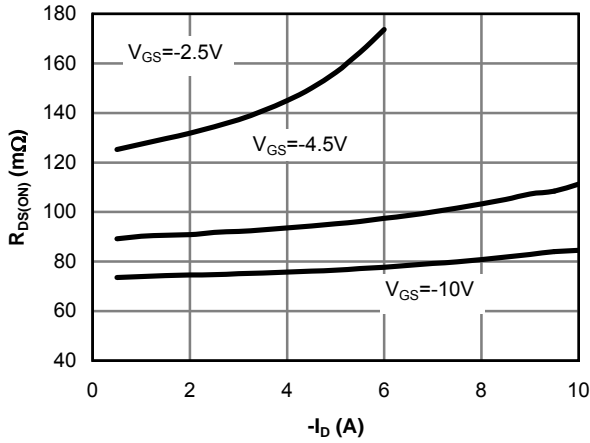


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

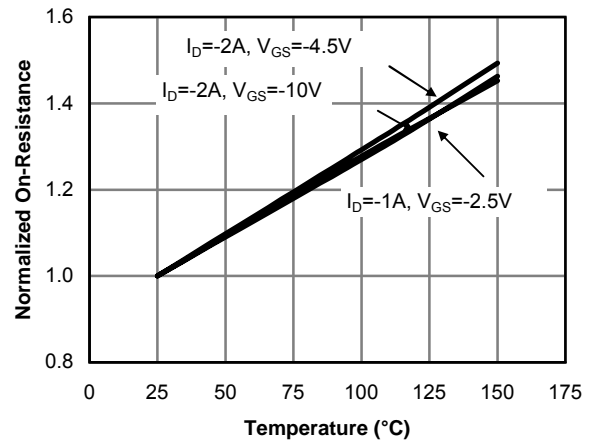


Figure 4: On-Resistance vs. Junction Temperature

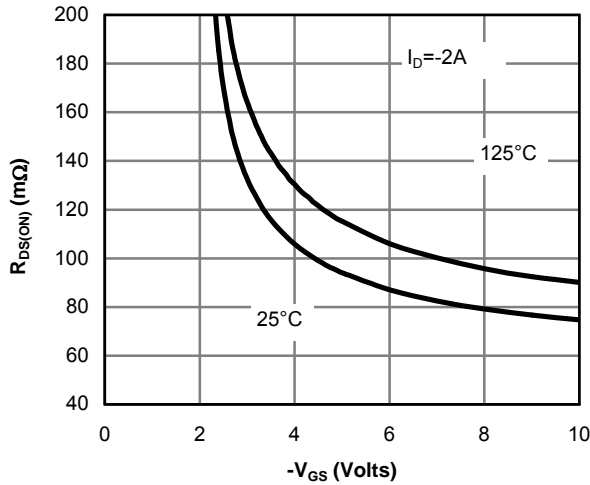


Figure 5: On-Resistance vs. Gate-Source Voltage

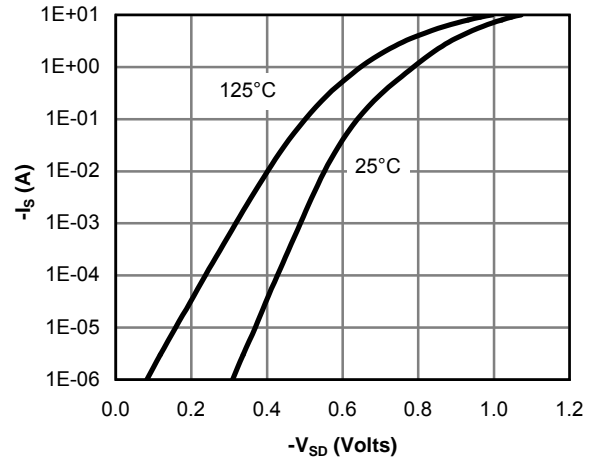


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

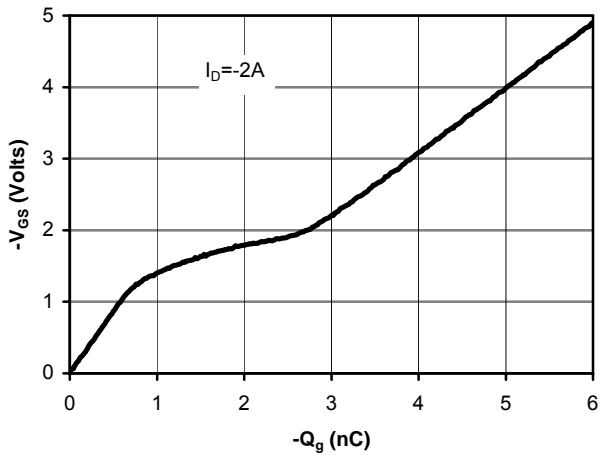


Figure 7: Gate-Charge Characteristics

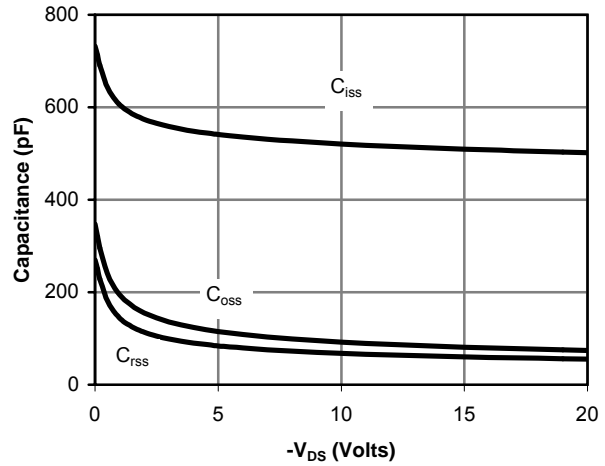


Figure 8: Capacitance Characteristics

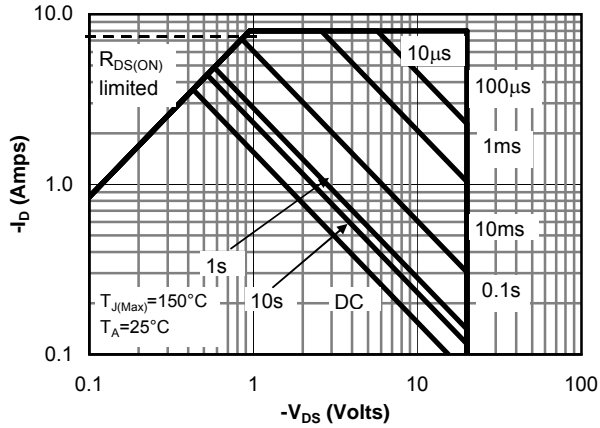


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

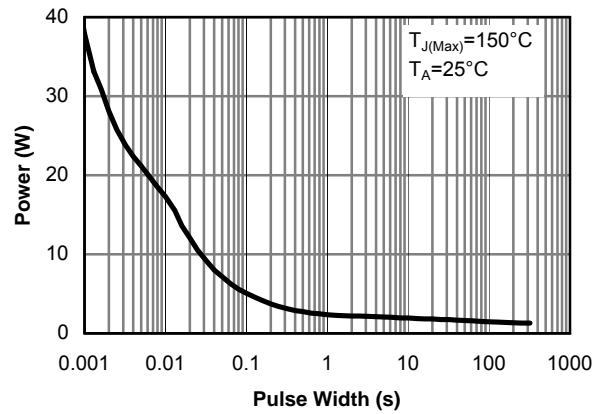


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

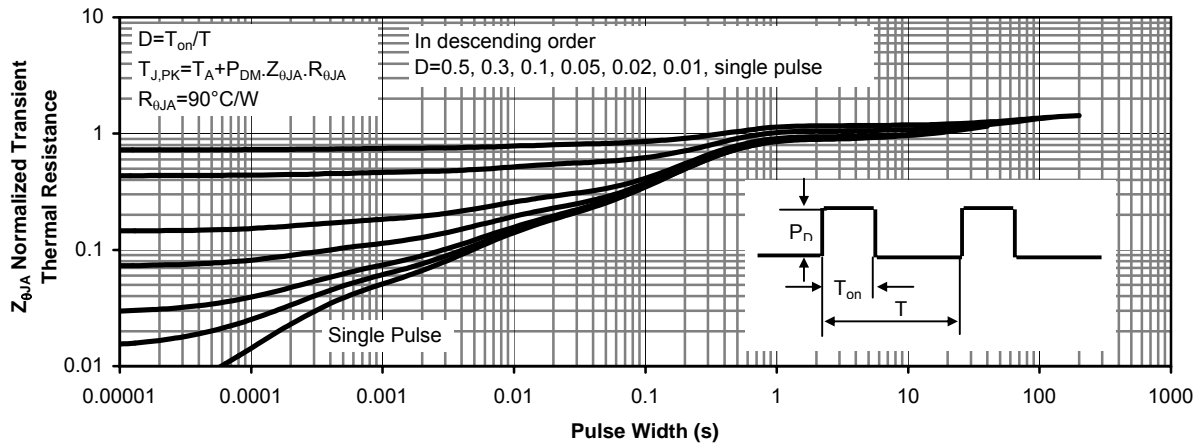


Figure 11: Normalized Maximum Transient Thermal Impedance